Abstracts

A low-power 15-GHz frequency divider in a 0.8-/spl mu/m silicon bipolar technology

H. Knapp, W. Wilhelm and M. Wurzer. "A low-power 15-GHz frequency divider in a 0.8-/spl mu/m silicon bipolar technology." 2000 Transactions on Microwave Theory and Techniques 48.2 (Feb. 2000 [T-MTT] (Mini-Special Issue on Research Reported at the 1999 Radio Frequency Integrated Circuits (RFIC) Symposium)): 205-208.

In this paper, we present a low-power static frequency divider with a divide ratio of eight. It operates up to 15 GHz, consuming only 22 mA from a 3.6-V supply. The chip is manufactured in a 0.8-/spl mu/m silicon bipolar production technology with a cutoff frequency of 25 GHz. The circuit has a single-ended input and output and is mounted in a six-pin SOT363 plastic package.

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